

UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

				•		
APPLICATION NO.		FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/017,033		12/14/2001	Hichem M'Saad	A6139/T43800	7470	
32588	7590	12/23/2004		EXAM	INER	
APPLIED 2881 SCOT		NALS, INC.	HOFFMAN	HOFFMANN, JOHN M		
SANTA CLARA, CA 95050				ART UNIT	PAPER NUMBER	
				1731		
					DATE MAILED: 12/23/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

		
	Application No.	Applicant(s)
	10/017,033	M'SAAD, HICHEM
Office Action Summary	Examiner	Art Unit
	John Hoffmann	1731
The MAILING DATE of this communication a Period for Reply	ppears on the cover sheet w	ith the correspondence address
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a right of the period for reply is specified above, the maximum statutory perions are provided to reply within the set or extended period for reply will, by stated that the period for reply will, by stated and the period for reply will, by stated the period for reply will, by stated and the period for reply will, by stated the period for reply will be period for reply will, by stated the period for reply will be period for reply will b	N. 1.136(a). In no event, however, may a reply within the statutory minimum of third will apply and will expire SIX (6) MON ute, cause the application to become AE	reply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).
Status		
1)⊠ Responsive to communication(s) filed on <u>27</u> 2a)□ This action is FINAL . 2b)⊠ The 3)□ Since this application is in condition for allow closed in accordance with the practice under	nis action is non-final. vance except for formal matt	ers, prosecution as to the merits is
Disposition of Claims		
4)⊠ Claim(s) 1-18 and 20 is/are pending in the a 4a) Of the above claim(s) is/are withden 5)□ Claim(s) is/are allowed. 6)⊠ Claim(s) 1-18 and 20 is/are rejected. 7)□ Claim(s) is/are objected to. 8)□ Claim(s) are subject to restriction and	rawn from consideration.	
Application Papers		•
9) The specification is objected to by the Examination The drawing(s) filed on is/are: a) and a specificant may not request that any objection to the Replacement drawing sheet(s) including the correction. The oath or declaration is objected to by the second sec	ccepted or b) objected to ne drawing(s) be held in abeyar ection is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a list	nts have been received. nts have been received in A iority documents have been eau (PCT Rule 17.2(a)).	pplication No received in this National Stage
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/06) Paper No(s)/Mail Date	Paper No(s	tummary (PTO-413) s)/Mail Date nformal Patent Application (PTO-152)

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 27 September 2004 has been entered.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

The factual inquiries set forth in *Graham* v. *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:

- 1. Determining the scope and contents of the prior art.
- 2. Ascertaining the differences between the prior art and the claims at issue.
- 3. Resolving the level of ordinary skill in the pertinent art.
- 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

Page 3

Art Unit: 1731

Claim 1 is_rejected under 35 U.S.C. 103(a) as being unpatentable over Zhong 6705124 in view of Shieh 6204200

1. (Currently Amended) A method for forming an optical waveguide on a substrate in a process chamber, the method comprising:

Zhong does not appear to disclose the use of a chamber. It would have been obvious to use a chamber so as to maintain the environment, prevent gases from escaping, and prevent contaminants from being incorporated in the product. Examiner gives official notice that process chambers are well known.

depositing an undercladding layer over the substrate;

forming a plurality of separated optical cores over the undercladding layer,

These two steps are disclosed at claim 9 of Zhong, as well as the figures.

the plurality of optical cores defining a sequence of gaps having a width between 1 and 2 um

The sequence of gaps is disclosed in various portions, for example see col. 2, line 11-26, and figure 1 of Zhong. The gap width is taught at col.5, line36 – among other places.

and an aspect ratio between 2: 1 and 7:1;

See Zhong, col. 5, line 37.

Art Unit: 1731

and depositing an uppercladding layer over the plurality of cores and within the gaps with a high-density plasma process that includes simultaneous deposition and sputtering components

See, Zhong, figure 6, col 5, lines 53-57, and col 6, lines 3-5 and elsewhere.

and having a deposition-sputter ratio between 3:1 and 10:1 to fill the gaps, wherein the deposition-sputter ratio is defined as the ratio of a sum of a net deposition rate and a blanket sputtering rate to the blanket sputtering rate for the high-density plasma process.

Zhong does not disclose the ratio. Although it has to be greater than 1:1 – otherwise nothing would get deposited. Shieh is cited because it shows that it is known that the claimed deposition-sputter ratio is a result effective variable when using HDP silica deposition and discloses a values that are consistent with applicant: see claim 8 of Shieh as well as col. 3, lines 1-57 and figure 6. On the basis of what is known to those in the high density plasma deposition art: it would have been obvious to have the claimed deposition-sputter ratio so as to be able to fill any gap between adjacent cores. Alternatively, it would have been obvious to perform routine experimentation to determine the optimal deposition-sputter ratio.

Art Unit: 1731

Claims 1 – 7, 13-15, 18, and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bazylenko 6154582, in view of Dragone 5136671, Shieh 6204200 and optionally in view of Zhong and Van Cleemput 5872058 or Roche 5913140,

The basic method is disclosed in Bazylenko at the paragraph spanning cols. 6-7, figure 1A and col. 2, line 56. However, the plurality of cores, the aspect ratio, the gap width and the deposition-sputter ratio is not taught. It is noted that it would have been obvious to put multiple cores on the substrate so as to have more pathways for light communication. Duplication of parts is rarely a patentable invention and Applicant has not indicated any evidence of non-obviousness. Furthermore multiple cores is conventional: see Dragone.

Moreover, Dragone discloses (col. 1, lines 42- 52) that the waveguides must be closely spaced, but that such causes crosstalk. It would have been obvious to perform routine experimentation to determine the optimal spacing between the waveguides to balance these two conflicting effects. As can be seen in Dragone, the cores are shown to get closer and closer – until they meet – it would be reasonable to expect that at some location before they meet, that the gap is 1-2 microns wide.

As an alternative combination: it would have been obvious to make the Dragone device by using the Bazylenko method for the advantages that Bazylenko discloses for example in col. 3.

Shieh is cited because it shows that it is known that the claimed depositionsputter ratio is a result effective variable when using HDP silica deposition and

Art Unit: 1731

discloses a values that are consistent with applicant: see claim 8 of Shieh as well as col.

3, lines 1-57 and figure 6.

Van Cleemput and Roche are optionally cited as showing that applicant's gap-fill problem and solutions are well known.

On the basis of what is known to those in the high density plasma deposition art: it would have been obvious to have the claimed deposition-sputter ratio so as to be able to fill any gap between adjacent cores. Alternatively, it would have been obvious to perform routine experimentation to determine the optimal deposition-sputter ratio.

As to the aspect ratio: it is clear that if one were to use the Bazylenko 4.5 micron cores with a 1-2 micron gap, that one would have an aspect ratio of 2.25:1 – 4.5:1. Van Cleemput, Zhong and Roche show that such aspect ratios are known to be filled with HDP.

Claim 2: see col. 2, lines 32-36 of Bazylenko.

Claim 3: col. 6, lines 22-25 of Bazylenko.

Claim 18: see col. 6, line 19 of Bazylenko.

Claim 4: The flow rates are not disclosed. It would have been obvious to have whatever flow rates in as desired – depending upon the scale of the operation/chamber. Clearly a small substrate would require a lower flow rate than a large substrate. Furthermore, it would have been obvious to perform routine experimentation to determine the optimal flow rates.

Claim 5: see col. 7, line 4 of Bazylenko.

Art Unit: 1731

Claim 6, Examiner gives Official notice that it is conventional to use inert gas in HDP process for any number of reasons: to flush, to act as a carrier gas, etc. It would have been obvious to use an inert gas for any of the well known reasons, with no new or unexpected results.

Claim 7: see col. 2, lines 34-35, and col. 6, lines 63-67 of Bazylenko: any amount would be obvious based on the scale of the operation, and the degree of doping desired.

Claim 13: based on col. 5, line 49 and col. 6, line 12 of Bazylenko, the power density appears to be only 4 W/cm2. It would have been obvious to perform routine experimentation to determine the optimal power, with no new or unexpected results. Furthermore, even if one was felt that they were limited to the disclosed power for the figure 1a of Bazylenko embodiment, such gives no indication as to what the power would be for the ECR (col. 6, line 19) alterative embodiment. It would have been obvious to perform routine experimentation to determine the optimal power for the ECR embodiment.

Claim 14: there is a bias applied: col. 6, lines 13-14. It would have been obvious to perform routine experimentation to determine the optimal bias power.

Claim 15: Bazylenko uses a pressure of 15 millitorr. It would have been obvious to perform routine experimentation to determine the optimal pressure in the ECR apparatus.

Claim 20: col. 6, lines 64-65 of Bazylenko discloses an index of 1.45 which is between 1.46 and 1.4473. 1.46 is "about 1.4443". There is no indication that the 1.45

obvious to have what ever index one desires, depending upon the particular optical device/characteristics one desires.

Claim 8 rejected under 35 U.S.C. 103(a) as being unpatentable over Bazylenko 6154582, in view of Dragone 5136671, Shieh 6204200 and optionally in view of Zhong and Van Cleemput 5872058 or Roche 5913140 as applied to claim 7 and further in view of Ngai 6451686.

In the HDP deposition art, SiF4 and CF4 are known equivalents for fluorine sources see col 13, lines 46-54 and col. 12, lines 33-37 (Ngai). IT would have been obvious to substitute equivalents in the Bazylenko method, depending upon which gases are most available.

Claims 9-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bazylenko 6154582, in view of Dragone 5136671, Shieh 6204200 and optionally in view of Zhong and Van Cleemput 5872058 or Roche 5913140 as applied to claim 2 above, and further in view of Imoto 4856859.

Bazylenko dose not disclose using phosphorous gas as claimed. Imoto discloses that one can dope cladding using the claimed gas: col. 4, lines 61-66 and col. 2, lines 20-28. It would have been obvious to include the claim gas depending upon what specific glass is desired and what particular properties one desires for the final

Art Unit: 1731

product. The particular flow rates would have been obvious depending upon the desired degree of doping, and the size of the substrate to be made.

For claim 11 – it would be obvious to include boron as claimed – if one desires the known properties that boron produces in the final product.

Zhong is cited as being an "optional" because it is not necessary to demonstrate the invention is obvious (in the event that Applicant swears behind the Zhong filing date.) However Zhong does show that it is known to use HPD to make conformal layers with glass that includes boron and phosphorous.

Claims 12 is rejected under 35 U.S.C. 103(a) as being unpatentable over Bazylenko 6154582, in view of Dragone 5136671, Shieh 6204200 and optionally in view of Zhong and Van Cleemput 5872058 or Roche and Imoto 4856859 as applied to claim 11 above, and further in view of Schneider 4557561.

The boron trifluoride is not taught. Col. 3, lines 29-40 of Schneider discloses using the boron trifluoride when making a glass: to 1) add fluoride, and 2) to add the boron as a dopant. It would have been obvious to use boron Trifluoride in the Bazylenko process so as to supply another dopant Boron, and to help incorporate fluorine into the glass – depending upon the desired optical/chemical properties the artisan wishes to have in the final product.

Claim 16 is rejected under 35 U.S.C. 103(a) as being unpatentable over Bazylenko 6154582, in view of Dragone 5136671, Shieh 6204200 and optionally in view of Zhong and Van Cleemput 5872058 or Roche 5913140 as applied to claim 1 above, and further in view of Rossman 6194038

Bazylenko discloses different operating parameters than is being claimed. However, Rossman recognizes that the same claimed operating parameters "greatly increases the deposition rate" (col. 2, lines 29-34) – among other advantages. See col. 3, lines 8-37 of Rossman which discloses the various parameters. Col. 2 lines 9-21 discloses that the process is of the same nature as applicants' and Bazylenko's. It would have been obvious to change the Bazlenko parameters/gases to be in line with the Rossman parameters/gases for any or all of the Rossman advantages.

Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over Bazylenko 6154582, in view of Dragone 5136671, Shieh 6204200 and optionally in view of Zhong and Van Cleemput 5872058 or Roche 5913140 as applied to claim 1 above, and further in view of Rossman 6194038 and Narita 6122934

For claim 17: Narita discloses the same problem that Applicant and Rossman notes: a gap between two close structures. Bazylenko does not disclose this problem. It would have been obvious to have as many cores/waveguides on the substrate as possible, so as to have a high a circuit density as possible. It would have been obvious to use the Rossman method of etching between gaps so as to create conformal layers,

Art Unit: 1731

and for the high deposition rate. It would have been further obvious to add an additional layer so as to protect the optical device as disclosed in the Narita Abstract.

Zhong is cited as being an "optional" because it is not necessary to demonstrate the invention is obvious (in the event that Applicant swears behind the Zhong filing date.) However Zhong does show that it is known to use HPD to make conformal layers with glass that includes boron and phosphorous.

Response to Arguments

Applicant's arguments filed 24 November 2004 have been fully considered but they are not persuasive.

It is argued that Bazylenko does not disclose multiple pathways. This is not very relevant because 1) various secondary references disclose that it is known 2) it is prima facie obvious to duplicate parts for duplicate effects. It is not invention to have multiple waveguides.

It is also argued that it doesn't seem to be reasonable to have multiple waveguides with Bazylenko's electro-optical transducer. Col. 3, lines 9-10 of Balzylenko discloses that the HDP process "has advantageous application for the fabrication of any optical device." It is largely irrelevant that one might not want more

Art Unit: 1731

than one waveguide on a specific device. Once would clearly not be limited to that one device.

It is further argued that Balzylenko does not disclose using deposition/sputter process for the cladding layer. As applicant points out, Balzylenko teaches using PECVD, this is sufficient in that this encompasses at least all PECVD methods that Balzylenko discloses. This includes the deposition/sputter process.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Soole and Dragone 5002350 are cited as disclosing features of applicant's invention.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to John Hoffmann whose telephone number is (571) 272 1191. The examiner can normally be reached on Monday through Friday, 7:00- 3:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Steve Griffin can be reached on 571-272-1189. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only.

For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

you have questions on access to the Private PAIR system, contact/the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

John Hoffmann

Primary Wkaminer

jmh